Paper id	Title of the paper	Category of the paper
1	Evolution, Current Status and Future Trend of RF Transistors	Advanced Devices
2	Noise Analysis for a SiGe HBT by Hydrodynamic Device Simulation	Modeling and Characterization
3	Knowing the Key Factors in RF Power Amplifier Design	Advanced Devices
. 4 .	Compact LDD/FD SOI CMOS Device Model Considering Energy Transport and Self Heating for SPICE Circuit Simulation	Modeling and Characterization
	Impact of Deep N-well Implantation on Substrate Noise Coupling and RF Transistor Performance for Systems-on-a-Chip Integration	ITRS Roadblocks, Models and Process Steps
6	Tunneling Phenomenon in SuperFlash Cell	CMOS and Memory Devices
7	Design Sensitivity in Quasi-One-Dimensional Silicon-Based Photonic Crystalline Waveguides	Advanced Devices
8	Failure Characterization of ESD Damage in Low Temperature Poly-Si TFTs	Sensors and Biosensors
9	Off-Leakage and Drive Current Characteristics of Sub-100-nm SOI MOSFETs and Impact of Quantum Tunnel Current	CMOS and Memory Devices
10	Fast CMOS-Integrated Finger Photodiodes for a Wide Spectral Range	Sensors and Biosensors
	Evaluation of Interface Trap Density in a SiGe/Si Heterostructure Using a Charge Pumping Technique and Correlation between the Trap Density and Low Frequency Noise in SiGe-Channel pMOSFETs	Modeling and Characterization
	Compact Breakdown Model for PD SOI NMOS Devices Considering BJT/MOS Impact Ionization for SPICE Circuit Simulation	Modeling and Characterization
13	A New Physical Modeling of Parasitic Capacitances of Deep-Submicron LDD MOSFETs	Modeling and Characterization
14	Dissipative transport in quantum wires	Modeling and Characterization
15	Influence of the Extrinsic Base on the Base Current Kink in SiGe BJTs	Modeling and Characterization
16	Automatic Order Reduction of Thermo-Electric Models for MEMS: Arnoldi versus Guyan	Sensors and Biosensors
17	Static and RF behaviour of short-gate Fully-Depleted Silicon-on-Insulator MOSFETs: numerical and experimental analysis	Modeling and Characterization
18 1	Small Signal Characterization of Thin Film Single Halo SOI MOSFET For Mixed Mode Analog and Digital Applications	Modeling and Characterization
19	Hot carrier reliability improvement of PMOS I/O's transistor in advanced CMOS technology	CMOS and Memory Devices
20	Reduction of Bitline to Control Gate leakage for improved embedded 0.18 um FLASH Yield and Reliability	CMOS and Memory Devices
	Reverse-Order Source/Drain (R-S/D) Combined with LDD Offset Spacer and Its Application to 50nm Physical-Gate-Length nMOSFETs	CMOS and Memory Devices
22	Comments on Existing 1/f Noise Models:Spice, HSPICE and BSIM3v3 for MOSFETs in Circuit Simulators	Modeling and Characterization
23	Micromachined Mercury Sensor	Sensors and Biosensors
24	Post-Process CMOS Front End Engineering With Focused Ion Beams	ITRS Roadblocks, Models and Process Steps
25	Degradation Dynamics for Deep Scaled p-MOSFET's during Hot-Carrier Stress	CMOS and Memory Devices
	A CMOS Photodiode Array with Linearized Spectral Response and Spatially Distributed Light Intensity Detection for the Use in Optical Storage Systems	Sensors and Biosensors
27	Nano crystal memory devices characterization using the charge pumping technique	Modeling and Characterization
28	Properties of Vacancies in Silicon Determined from LaserAnnealing Experiments	Modeling and Characterization
29	Gate and Drain Bias Dependences of 1/f Noise Amplitude in MOSFETs in the Linear and Saturation Regions	Modeling and Characterization
30	A Tuneable Metal Gate Work Function Using Solid State Diffusion of Nitrogen	ITRS Roadblocks, Models and Process Steps

Paper id	Title of the paper	Category of the paper
31	High reproducible ideal SiC Schottky rectifiers by controlling surface preparation and thermal treatments	Advanced Devices
32	Impact of ALCVD and PVD Titanium Nitride Deposition on Metal Gate Capacitors	ITRS Roadblocks, Models and Process Steps
33	Self-Consistent Solution of the Schrodinger and Poisson Equations for Accumulated MOS Capacitors with Ultra-thin Layers	Modeling and Characterization
34	Extraction of Si-SiO2 interface trap densities in MOSFET's with oxides down to 1.3 nm thick	Modeling and Characterization
35	Modeling of Large-Area nMOS Devices for Smart-Power Applications	Modeling and Characterization
37	Performance and reliability of high density flash EEPROMs under CHISEL programming operation	CMOS and Memory Devices
38	Extraction method for the impact-ionization multiplication factor in silicon at large operating temperatures	Modeling and Characterization
40	Improved Isolated RESURF Technology for a Multi Power BCD Process	Advanced Devices
41	Threshold Variations for Undoped Double-Gate MOSFET's	Modeling and Characterization
42	Effects of Boron and Germanium Base Profiles on SiGe and SiGe:C BJT Characteristics	Modeling and Characterization
43	Simulation and Modeling of Nanocrystalline Silicon Thin Film Transistors	Modeling and Characterization
44	Ar Sputter Etch to Improve the Insulator Quality in Metal Capacitors	ITRS Roadblocks, Models and Process Steps
45	SILC Measurements of Thin SiO2 at Low Voltages: High-resolution measurements and interpretation	Modeling and Characterization
46	Design Guidelines for Linear Amplification and Low-insertion loss in 5-GHz-band SOI Power MOSFETs	Advanced Devices
47	Coupled Monte Carlo Simulation of Si and SiO2 Transport in MOS Transistors	Modeling and Characterization
48	Metal Rings as Quantum Bits	Modeling and Characterization
49	An Ultra-Thin Polycrystalline-Silicon Thin-Film Transistor with SiGe Raised Source/Drain	Sensors and Biosensors
50	Investigation of performance improvement and gate-to-junction leakage reduction for the 90nm CMOS gate stack architecture	CMOS and Memory Devices
51	Impact of Post Metal Etch Resist Strip in Plasma on Plasma Charge-Induced Erosion of Tungsten-Plugs	ITRS Roadblocks, Models and Process Steps
52	High-Frequency Bipolar Transistor Noise Modeling	Modeling and Characterization
53	Future Trends in Intelligent Interface Technologies for 42V Battery Automotive Applications	Advanced Devices
54	Suppression of CoSix Induced Leakage Current using Novel Capping Process for Sub-0.10um node SRAM Cell technology	ITRS Roadblocks, Models and Process Steps
55	On the origin of the 1/f1.7 noise in deep submicron partially depleted SOI transistors	Modeling and Characterization
56	Monitoring Flash EEPROM Reliability by Equivalent Cell Analysis	CMOS and Memory Devices
57	Fabrication of 0.1-um pMOSFETs with SiGe-Channel and Elevated B-Doped SiGe Source and Drain Layers	CMOS and Memory Devices
59	Temperature-Dependent Characteristics of an n+-InGaAs/n-GaAs Composite Doped Channel (CDC) Heterostructure Field-Effect Transistor	Advanced Devices
60	Impact of Scaling Down from 0.25um to 0.18um CMOS Technology on 1/f Noise: Characterisation and Modelling	Modeling and Characterization
61	On the n+-GaAs/p+-InGaP/nGaAs High-Barrier Camel-Like Gate Transistor for High-Breakdown, Low-Leakage and High-Temperature Operations	Advanced Devices
62	Antimony as Substitute for Arsenic to Eliminate Enhanced Diffusion Effects	ITRS Roadblocks, Models and Process Steps
63	An InGaP/GaAs Resonant-Tunnelling Bipolar Transistor (RTBT) with Multiple Negative-Differential-Resistance (MNDR) Phenomena	Advanced Devices
64	Characteristics of Polysilicon Resistors for Sub-Quarter Micron CMOS Applications	Modeling and Characterization
65	Clamped-Clamped Beam Micro-Mechanical Resonators in Thick-Film Epitaxial Polysilicon Technology	Sensors and Biosensors

Paper id	Title of the paper	Category of the paper
66	A Viable Self-aligned Bottom-Gate MOSFET Technology for High Density and Low Voltage SRAM	CMOS and Memory Devices
67	Impact of Tunnel Oxide Thickness on Erratic Erase in Flash Memories	CMOS and Memory Devices
68	Inversion Layer Quantization Impact on the Interpretation of 1/f Noise in Deep Submicron CMOS Transistors	Modeling and Characterization
69	Variable-Gain Inversion Layer Emitter Phototransistor in CMOS Technology	Sensors and Biosensors
70	Effect of Pulsed Stress on Leakage Current In MOS Capacitors For Non-Volatile Memory Applications	CMOS and Memory Devices
71	LOW PINCH-OFF VOLTAGE AMORPHOUS SILICON JUNCTION FIELD-EFFECT TRANSISTOR: SIMULATION AND EXPERIMENT	Sensors and Biosensors
72	Microwave noise Modeling of the 0.18um Gate Length Mosfets with a 60GHz cut-off frequency	Modeling and Characterization
73	Reduction of parasitic capacitance in vertical MOSFET's by fillet local oxidation (FILOX)	ITRS Roadblocks, Models and Process Steps
74	Modeling the C-V Characteristics of Heterodimensional Schottky Contacts	Modeling and Characterization
75	Application of Polycrystalline SiGe for Gain Control in SiGe Heterojunction Bipolar Transistors	Advanced Devices
76	Photoelectric and Tensometric Properties of a Metal Phthalocyanine-Silicon Junctions	Sensors and Biosensors
77	Implantation Dose Profiling by MOS C-V Measurements	Modeling and Characterization
78	Characteristics of HfO2 pMOSFET with ultrashallow junction prepared by plasma doping and laser annealing	ITRS Roadblocks, Models and Process Steps
79	Compact Quantum Mechanical Device Models for MOSFETs in Gigascale Integration(GSI)	Modeling and Characterization
80	Transmission Coefficient Estimation for High-K Gate Stack Evaluation	Modeling and Characterization
81	Diffusion Suppression in Silicon by Substitutional C Doping	ITRS Roadblocks, Models and Process Steps
82	Low Power, 3-bit CMOS Pipeline ADC with Reduced Complexity Flash Architecture	Advanced Devices
83	Device Model of Integrated QWIP-HBT-LED Pixel for Infrared Focal Plane Arrays	Sensors and Biosensors
84	Impact of p-Well Implantation Parameters on Junction Leakage	ITRS Roadblocks, Models and Process Steps
85	High Temperature CMOS Process with Dielectric Isolation	ITRS Roadblocks, Models and Process Steps
86	Impact of source/drain implants on threshold voltage matching in deep sub-micron CMOS technologies	ITRS Roadblocks, Models and Process Steps
87	Fast polymer integrated circuits based on a polyfluorene derivative	Sensors and Biosensors
88	Highly Extendible Memory Cell Architecture for Reliable Data Retention Time for 0.10mm Technology Node and beyond	CMOS and Memory Devices
89	Deep Trap Modelling and Transient Measurements of a-Si:H p-i-n Diodes	Modeling and Characterization
90	Study of Hot-spot Phenomena in Cellular Power Transistors by Analytical Electro-Thermal Simulation	Advanced Devices
91	Integrated Si-based Opto-Couplers: a Novel Approach to Galvanic Isolation	Sensors and Biosensors
92	Numerical and Analytical Study of 6H-SiC Detectors with High UV Performance	Sensors and Biosensors
94	Pseudo Dynamic Gate Design based on the Resonant Tunneling-Bipolar Transistor (RTBT)	Advanced Devices
95	A New Improved Model for LDMOS Transistors under Different Gate and Drain Bias Conditions	Modeling and Characterization
96	Lithography Independent Fabrication of Nano-MOS-Transistors with W = 25 nm and L = 25 nm	ITRS Roadblocks, Models and Process Steps
97	Investigating 50nm channel length vertical MOSFET containing a dielectric pocket, in a circuit environment	Modeling and Characterization
98	A method for extraction of power dissipating sources from interferometric thermal mapping measurements	Modeling and Characterization
99	Cost Effective Implementation of a 90 V RESURF P-type Drain Extended MOS in a 0.35 um Based Smart Power Technology	Advanced Devices

Paper id	Title of the paper	Category of the paper
100	Characteristics of Sub-100nm High-k Gate Dielectrics MOSFETs With Different Source/Drain Structure	ITRS Roadblocks, Models and Process Steps
101	Stability of High-k Thin Films for Wet Process	ITRS Roadblocks, Models and Process Steps
102	Implementing Self-Heating Effects into a Volterra Simulator	Modeling and Characterization
103	Thick Film Gamma Radiation Sensors with Sensitive Layers of NiO and La2O3–Fe2O3 Mixture	Sensors and Biosensors
104	Scaling considerations for fully-depleted SOI transistors down to the 20nm gate length regime	Modeling and Characterization
105	Stability of High-k Thin Films in Moisture Ambience - The Effect of Dissolution Gas from Acryl Apparatus -	ITRS Roadblocks, Models and Process Steps
106	Electrical Characteristics Improvement of Dy2O3 Thin Films by In-situ Vacuum Anneal	ITRS Roadblocks, Models and Process Steps
107	Use of Oxynitride Dielectric to Maximise the Growth Rate of Selective Epitaxial Base Layer in a Self-Aligned Double-Polysilicon SiGe Bipolar Transistors	ITRS Roadblocks, Models and Process Steps
108	Annealing Condition Dependence of Electrical Characteristics.	ITRS Roadblocks, Models and Process Steps
109	Identification of Critical Parameters for Plasma Process-Induced Damage in 130 and 100 nm CMOS Technologies	ITRS Roadblocks, Models and Process Steps
110	Passive DNA Sensor with Gold Electrodes Fabricated in a CMOS Backend Process	Sensors and Biosensors
111	Electrical Characteristics of Gd2O3 thin film deposited on Si substrate.	ITRS Roadblocks, Models and Process Steps
112	Electrical Characterisation of Silicon-Rich-Oxide Based Memory Cells Using Pulsed Current-Voltage Techniques	CMOS and Memory Devices
113	Characteristics of High-k Gd2O3 Films Deposited on Different Orientation of Si Substrate	ITRS Roadblocks, Models and Process Steps
114	Accurate modeling of Quantum-Dot based Multi Tunnel Junction Memory: Optimization and process dispersions analyzes for DRAM applications	Modeling and Characterization
115	TCAD Based Design Methodology for Substrate Current Control in Smart Power ICs	Advanced Devices
116	Numerical simulation of parameters of ZnCdHgTe films and	Sensors and Biosensors
117	Simulated influence of bulk traps on the subthreshold characteristics of an organic field effect transistor	Sensors and Biosensors
118	Investigation of the Thermal Noise of MOS Transistors under	Modeling and Characterization
119	Accurate Delay Metric for On-chip Resistive Interconnect	Modeling and Characterization
120	Temperature-Independence-Point Properties for 0.1um-scale Pocket-Implant Technologies and the Impact on Circuits Design	CMOS and Memory Devices
121	Low frequency noise in 0.12 µm Partially and Fully Depleted SOI technology	Modeling and Characterization
122	A 12Volt, 12GHz Complementary Bipolar Technology for High Frequency Analogue Applications	Advanced Devices
123	Comparison of the Gate Tunneling Current in Ultrathin-Oxide Inversion and Accumulation MOSFETs	CMOS and Memory Devices
124	Optimising High-Voltage Devices in a Smart Power Technology, using the RESurF-effect and TCAD.	Advanced Devices
125	Design and simulation of an a-Si:H/GaAs heterojunction bipolar transistor	Modeling and Characterization
126	Gate dielectrics for high performance and low power CMOS SoC applications	ITRS Roadblocks, Models and Process Steps
127	Efficient Monte Carlo Simulation of Tunnel Currents in MOS Structures	Modeling and Characterization
128	Improved Modified Local Density Approximation for the Modeling of Size Quantization in pMOSFETs	Modeling and Characterization
129	Voltage-controlled substrate structure for integrated inductors in standard digital CMOS technologies	Advanced Devices

Temperature Effects of Low Noise InGaP/InGaAs/GAAs PHEMTs Monotific Integration of a Novel Microfluidic Device with Silicon Light Emitting Diode-Antifuse and Sensors and Biosensors	Paper id	Title of the paper	Category of the paper
Photodetector Serious	130	Temperature Effects of Low Noise InGaP/InGaAs/GaAs PHEMTs	Advanced Devices
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Influence of Deping Profile and Halo Implantation on the Threshold Voltage Mismatch of a 0.13 um CMOS Culomb Blockade in Thin SOI Nanodevices Modeling and Characterization Mixing Sources of Intrinsic Parameter Fluctuations in the Simulation of Sub-100nm MOSFETS Modeling and Characterization Mixing Sources of Intrinsic Parameter Fluctuations in the Simulation of Sub-100nm MOSFETS Modeling and Characterization Siep MOSFETS Fabricated on Novel SiGe Virtual Substrates Grown on 10µm x 10µm Pillars. CMOS and Memory Devices A Robust and Physically Based Compact SOI-LDMOS Model Quantum Dot Materials and Devices for Light Emission in Silicon Sensors and Biosensors Interpret Compact RF-Noise Modelling for Deep Sub-Micron MOSFETS Modeling and Characterization ITRS Roadblocks, Models and Process Steps Reducing the Threshold Voltage Deviation for sub-100nm Transistors using Midbandgap-Gatematerials ITRS Roadblocks, Models and Process Steps Reducing the Threshold Voltage Deviation for sub-100nm Transistors using Midbandgap-Gatematerials ITRS Roadblocks, Models and Process Steps Reducing the Threshold Voltage Deviation for sub-100nm Transistors using Midbandgap-Gatematerials ITRS Roadblocks, Models and Process Steps Reducing the Threshold Voltage Deviation for sub-100nm Transistors using Midbandgap-Gatematerials ITRS Roadblocks, Models and Process Steps Reducing the Threshold Voltage Deviation for sub-100nm Transistors using Midbandgap-Gatematerials ITRS Roadblocks, Models and Process Steps Reducing the Threshold Voltage Deviation for sub-100nm Transistors in Bipolari/CMOS/DMOS technology Advanced Devices Modeling and Characterization Advanced Devices Process and device simulation of power VDMOS transistors in Bipolari/CMOS/DMOS technology Advanced Devices Woltage Brown Transistors in Contracterization Method for Bias-Dependent Drift Series Resistance of HV Modeling and Characterization ITRS Roadblocks, Models and Process Steps Universal Test Structure for In-situ Measurements of interface Recombination During Surface Treatme	132	Quasi-analytical modelling of drain current and conductance of Single Electron Transistors with MIB	Modeling and Characterization
Technology Technology Technology Technology Technology Coulomb Blockade in Thin SOI Nanodevices Modeling and Characterization Mixing Sources of Intrinsic Parameter Fluctuations in the Simulation of Sub-100nm MOSFETs Modeling and Characterization Mosing Sources of Intrinsic Parameter Fluctuations in the Simulation of Sub-100nm MOSFETs Modeling and Characterization Improved Compact RF-Noise Modelling for Deep Sub-Micron MOSFETs Modeling and Characterization Modeling and Characterization Modeling and Characterization fras Reducing the Threshold Voltage Deviation for sub-100nm Transistors using Midbandgap-Gatematerials TRS Roadblocks, Models and Process Steps Reducing the Threshold Voltage Deviation for sub-100nm Transistors using Midbandgap-Gatematerials TRS Roadblocks, Models and Process Steps Realization of a SCR on an Epitaxial Substrate Using All Thermomigration Realization of a SCR on an Epitaxial Substrate Using All Thermomigration Realization of a SCR on an Epitaxial Substrate Using All Thermomigration Advanced Devices Modeling and Characterization Process and device simulation of power VDMOS transistors in Bipolar/CMOS/DMOS technology Modeling and Characterization Modeling and Characterization Transity of 80V Vertical n-DMOS in a 0.35mc MOS Technology Advanced Devices Tunnelling and impact ionization in scaled double doped PHEMTs Modeling and Characterization Modeling and Characterization Transity of the Characterization Method for Bias-Dependent Drift Series Resistance of HV MOSFETs Integrated Photodiodes in Standard BiCMOS Technology Impact of statistical threshold voltage fluctuation and quantum mechanical effects on cross circuits with gigablic fluctuation and quantum mechanical effects on cross circuits with gigablic fluctuation and th	133	Gate Material Properties Induced 0.25µm SRAM Marginality	CMOS and Memory Devices
Mixing Sources of Intrinsic Parameter Fluctuations in the Simulation of Sub-100nm MOSFETs SiGe pMOSFETs Fabricated on Novel SiGe Virtual Substrates Grown on 10µm x 10µm Pillars. OMOS and Memory Devices OMOS and Devices OMOS and Memory Devices	134	, ,	CMOS and Memory Devices
SiGe pMOSFETs Fabricated on Novel SiGe Virtual Substrates Grown on 10 µm x 10 µm Pillars. CMOS and Memory Devices A Robust and Physically Based Compact SOI-LDMOS Model Modeling and Characterization Quantum Dot Materials and Devices for Light Emission in Silicon Sensors and Biosensors Integrated Physically Based Compact RF-Noise Modelling for Deep Sub-Micron MOSFETS Modeling and Characterization Ith Reducing the Threshold Voltage Deviation for sub-100nm Transistors using Midbandgap-Gatematerials ITRS Roadblocks, Models and Process Steps Electron Transport in Semiconductor-Insulator Structures Using the Full-Band Dispersion Relation of Si and SiO2 SiO2 Modeling and Characterization ITRS Roadblocks, Models and Process Steps Realization of a SCR on an Epitaxial Substrate Using Al Thermomigration Advanced Devices Advanced Devices Advanced Devices Realization of a SCR on an Epitaxial Substrate Using Al Thermomigration Advanced Devices Realization of a SCR on an Epitaxial Substrate Using Al Thermomigration Advanced Devices Realization of a SCR on an Epitaxial Substrate Using Al Thermomigration Advanced Devices Realization of a SCR on an Epitaxial Substrate Using Al Thermomigration Advanced Devices Realization of a SCR on an Epitaxial Substrate Using Al Thermomigration Advanced Devices Modeling and Characterization Modeling and Characterization Rechanisms of doppart redistribution and retention in Silicon following ultra-low energy Boron implantation and exciment laser annealing Universal Test Structure and Characterization Method for Bias-Dependent Drift Series Resistance of HV Modeling and Characterization Modeling and Characterization TRS Roadblocks, Models and Process Steps Realization of statistical threshold voltage fluctuation and quantum mechanical effects on cross circuits with gigabit Integrated Photodiodes in Standard BiCMOS Technology Sensors and Biosensors Repaired of stochastic dopant variation and the copper size effect on gigasc	135	Coulomb Blockade in Thin SOI Nanodevices	Modeling and Characterization
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167	Substrate bias effect on cycling induced performance degradation of Flash EEPROMs	CMOS and Memory Devices
168	A Novel Dynamic Threshold Operation Using the Electrically Induced Junction MOSFET in the Deep Sub- micrometer CMOS Regime	CMOS and Memory Devices
169	Design of a Remote Control System for a Wireless Microrobot	Sensors and Biosensors
170	Optoelectronics properties of FTO/SRO/Si radiation sensors	Sensors and Biosensors
171	The Advanced RESURF Structure to improve On-Resistance in BCDMOS	Advanced Devices
172	A Comparative Analysis of Active and Passive Pixel CMOS Image Sensors	Sensors and Biosensors
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174	Through-Wafer Copper Electroplating for RF Silicon Technology	ITRS Roadblocks, Models and Process Steps
175	A new approach to failure analysis and yield enhancement of very large-scale integrated systems	Modeling and Characterization
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179	Monte Carlo Simulation of Program and Erase Charge Distributions in NROM(TM) Devices	Modeling and Characterization
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182	Temperature dependence of the hard breakdown current of MOS capacitors	Modeling and Characterization
183	Effects of random discrete impurities in ultra-short MOSFET using 3D Monte Carlo simulation	Modeling and Characterization
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185	Effects of Stress-Induced Bandgap Narrowing on Reverse-Bias Junction Behavior	Modeling and Characterization
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193	New mechanism of body charging in partially depleted SOI-MOSFETs with ultra-thin gate oxides	CMOS and Memory Devices
194	Channel architecture optimisation to reduce RNCE of deep sub-micron devices	ITRS Roadblocks, Models and Process Steps
195	Gate oxide process impact on RNCE for advanced CMOS transistors	ITRS Roadblocks, Models and Process Steps
196	On the High Temperature Operation of High Voltage Power Devices	Advanced Devices
197	Lateral Trench Gate Super-Junction SOI-LDMOSFETs with Low On-Resistance	Advanced Devices
198	Three-Dimensional Analysis of a MAGFET at 300 K and 77 K	Modeling and Characterization
199	Substrate Effects on the Small-Signal Characteristics of SOI MOSFETs	CMOS and Memory Devices
200	Volume shrinking in Micro-Fluidic Self-Assembly	Sensors and Biosensors
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202	LaNixFe1-xO3 thin films: p-type ethanol sensors	Sensors and Biosensors
203	Channel Engineering Study for 50 nm P-Channel MOSFET	CMOS and Memory Devices

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205	The Four-Gate Transistor	Advanced Devices
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207	Hybrid metal-organic photodetectors based on a new class of metal-dithiolenes	Sensors and Biosensors
208	An Improved Model for Electron Mobility Degradation by Remote Coulomb Scattering in Ultra-Thin Oxide MOSFETs	Modeling and Characterization
209	An Algorithm for Smoothing Three-Dimensional Monte Carlo Ion Implantation Simulation Results	Modeling and Characterization
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211	50nm Schottky Barrier CMOS with Conventional Silicide	CMOS and Memory Devices
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213	A MOS Nanogap Device Structure for Characterisation of Nano-scale Objects	Advanced Devices
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235	High-performance Silicon-On-Glass VDMOS transistor for RF-power applications	Advanced Devices

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238	Thermal Nitridation of Chemical Dielectrics as an Easy Approach to Ultra-thin Gate Oxide Processing	ITRS Roadblocks, Models and Process Steps
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242	Reduction of Short-Channel Effects and Improvement in Microwave Characteristics for V-groove Gate Pseudomorphic Doped-Channel HFET with Dual V-groove Gate Structure	Advanced Devices
243	A Novel General Direct Extraction Technique Used For a RF MOSFET Small-Signal Equivalent Circuit	Modeling and Characterization
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247	Controlling STI-related parasitic conduction in 90 nm CMOS and below	CMOS and Memory Devices
248	CMOS circuit analysis with luminescence measurements and simulations	Modeling and Characterization
249	ZrO2 gate dielectrics prepared by e-beam deposition of Zr and YSZ films and post annealing processes	ITRS Roadblocks, Models and Process Steps
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256	Reliability and Retention Study of Nanocrystal Cell Array	CMOS and Memory Devices
257	Vertical high voltage devices on thick SOI with back-end trench formation	Advanced Devices
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260	A Biosensor for Direct Detection of DNA Sequences Based on Capacitance Measurements	Sensors and Biosensors
261	A New Compact Horizontal Current Bipolar Transistor (HCBT) Fabricated in (110) Wafers	ITRS Roadblocks, Models and Process Steps
262	A Novel CMOS Compatible Top-Floating-Gate Flash EEPROM Cell.	CMOS and Memory Devices
263	Improvement in the prediction of Boron diffusion during a Spike Annealing for Ultra-Shallow Junctions	Modeling and Characterization
264	Tunnel Barrier Properties of Polycrystalline-Si Single-Electron Transistor	Modeling and Characterization
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266	Influence of source-drain tunneling on the subthreshold behavior of sub-10nm double-gate MOSFETs	CMOS and Memory Devices
267	Benchmarking of Table Methods for MOSFET modelling	Modeling and Characterization
268	Improved Deep Sub-micron CMOS Ring Oscillator Performance with n-HDD and n-LDD P+ + As+ Co-Implant	CMOS and Memory Devices

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270	Suitability of Scaled SOI CMOS for High-Frequency Analog Circuits	CMOS and Memory Devices
271	Influence of the Inner Miller-Effect on the Input Capacitance of CMOS Transistors	Modeling and Characterization
272	High Hot-Carrier and ESD Immunity Device for High-Voltage I/O NMOSFETs in 0.1-um CMOS Technology	CMOS and Memory Devices
273	Scaling of MOSFET Transconductance with Gate Oxide Thickness and Effect of Remote Charge Scattering	Modeling and Characterization
274	A Novel MEMS Technological Platform Aimed at RF Applications	Sensors and Biosensors
275	Si Nanocrystal Based Memory Structures by Ultra Low Energy Implantation for Low Voltage/Low Power Applications	CMOS and Memory Devices
276	Source/Drain Parasitic Resistance Role and Electrical Coupling Effect in sub 50nm MOSFET Design	Modeling and Characterization
277	Fast Algorithm for Clock Grid Simulation	CMOS and Memory Devices